New Jersey Semi-Conductor Products, Inc.

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2N3055 H

SILICON N-P-N GENERAL-PURPOSE

2N3055 are Hometaxial-base** types useful for power-switching circuits, for series- and shunt-regulator driver and output stages, and for high-fidelity amplifiers.

**"Hometaxial" was coined by RCA from "homogeneous" and "axial" to describe a single-diffused transistor with a base region of homogeneous-resistivity silicon in the axial direction (emitter-to-collector).

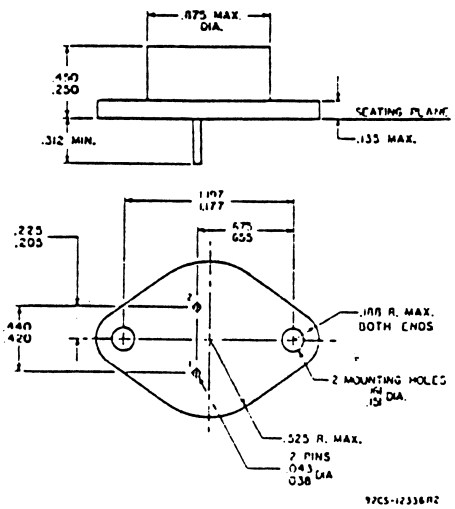
MAXIMUM RATINGS

Absolute-Maximum Values:		2N3055	
COLLECTOR-TO-BASE VOLTAGE	V_{CBO}	100	V
COLLECTOR-TO-EMITTER VOLTAGE:			
With −1.5 V (V_{BE}) of reverse bias	$V_{CEV(sus)}$	100	V
With external base-to-emitter resistance (R_{BE}) = 10 Ω	$V_{CER(sus)}$	—	V
= 100 Ω	$V_{CER(sus)}$	70	V
With base open	$V_{CEO(sus)}$	60	V
EMITTER-TO-BASE VOLTAGE	V_{EBO}	7	V
COLLECTOR CURRENT	I_C	15	A
BASE CURRENT	I_B	7	A
TRANSISTOR DISSIPATION:	P_T		
At case temperatures up to 25°C		115	W
At free-air temperatures up to 25°C		—	W
		—	W
		—	W

TEMPERATURE RANGE:		
Storage & Operating (Junction)	← −65 to 200 →	°C
LEAD OR PIN TEMPERATURE (During soldering): At distance ≥ 1/32" from seating plane for 10 s max.	235	°C

DIMENSIONAL OUTLINE

JEDEC No. TO-3



Dimensions in Inches

Quality Semi-Conductors